

Title: FABRICATION METHOD FOR A SEMICONDUCTOR STRUCTURE HAVING A PARTLY FILLED TRENCH

Applicant: Hansel et al. Serial No. 10/660,091 Ref No.: 1406/166

FIG 1A

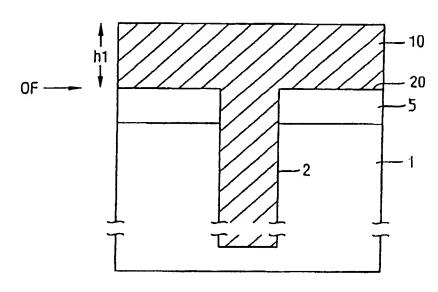
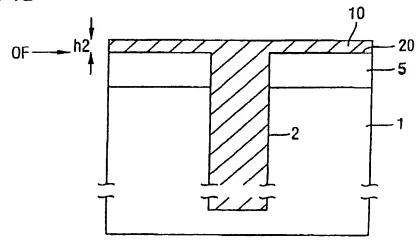


FIG 1B



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FIG 1C

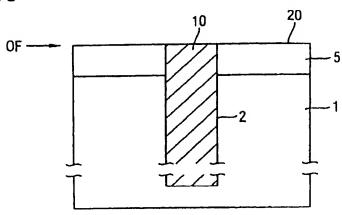
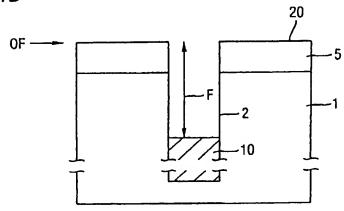


FIG 1D



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FIG 2A

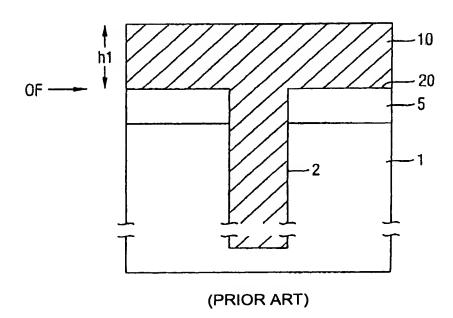


FIG 2B 10 20 OF δ} Δ1 (PRIOR ART)

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